Abstract

This paper proposes a new design of 2T AND gate. Performance comparison of proposed gate with existing 2T GDI technique is presented. Different methods have been compared with respect to the number of devices, power consumption, power-delay product, temperature sustainability and noise immunity in order to prove the superiority of proposed design over existing 2T gate design. The simulation has been carried out on Tanner EDA tool on BSIM3v3.
90nm technology.

**Reference**


**Index Terms**

Computer Science Wireless

**Key words**

New Efficient 2T Gate Design